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Characterization of Porous Silicon- based Active and Passive Electronic Devices

THESIS

*Submitted to Faculty of Science-Ain Shams University in partial fulfillment for
Degree of master in Physics*

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2018

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Grant Date: 2018

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Contents

Acknowledgment	I
List of Tables	III
List of Figures	VIII
Abstract	IX

Chapter 1:

Introduction

1.1. <i>Active device</i>	1
1.1.1. Solar cell.....	1
1.2. Passive device	3
1.2.1. Antireflection coating material (ARC)	4
1.3. <i>Historical review</i>	4
1.4. <i>Motivation for this work</i>	5
1.5. <i>Aim of work</i>	7
1.6. <i>Thesis outlines</i>	8

Chapter 2:

Theoretical background and literature review

2.1. <i>Photovoltaic</i>	11
2.2 Semiconductor	12
2.2.1 <i>Energy bands in semiconductor</i>	13
2.2.2. <i>Charge carriers in semiconductor</i>	14
2.2.2.1 Charge Generation.....	14
2.2.2.2 Charge Separation	15
2.2.2.3 Charge Transport.....	15

2.2.3 Direct and Indirect Semiconductors	16
2.4 Semiconductor Junctions	18
2.4.1 semiconductor-metal junctions.....	18
2.4.1.1 Shottky junction.....	18
2.4.1.2 Rectifying Contacts.....	21
2.4.1.3 Ohmic contact.....	23
2.4.2 semiconductor- semiconductor junctions.....	25
2.4.2.1 P-n Junctions	25
2.4.2.2 Heterojunctions	26
2.4.2.3 Homojunction	27
2.5 Ideal Diode Behavior	28
2.6 Characterization methods.....	31
2.6.1 I-V characteristics.....	31
2.6.2 Spectral response and quantum efficiency.....	33
2.7 Silicon solar cell.....	35
2.7.1 Basics of silicon solar cell.....	35
2.7.1.1 Damage etch and texture.....	35
2.7.1.2 Diffusion.....	36
2.7.1.3 Antireflection coating.....	36
2.7.1.4 Contact formation.....	37

2.8 Silicon dioxide as antireflection coating in solar cell manufacturing.....	37
2.9 Porous silicon as antireflection coating in solar cell manufacturing	38
2.10 Porous silicon.....	39
2.10.1 Introduction.....	39
2.10.2 Basics (fundamentals) of porous silicon	40
2.10.2.1 Fabrication techniques (How PS is made?).....	40
2.10.2.2 Experimental setup and terminology for photo-electrochemical etching of PS.....	41
2.10.3 Pore formation.....	42
2.10.4 Mechanism of electrochemical dissolution	44
2.10.5 Formation models	46
2.10.6 Effect of anodization conditions (parameters).....	49
2.10.7 Classification of Geometry and Morphology for Porous Silicon.....	52
2.10.8 Material properties	54
2.10.8.1 Physical properties	54
2.10.8.1.1 Quantum confinement model.....	54
2.10.8.2 Optical properties.....	56

2.10.8.2.1 Refractive index.....	56
2.10.8.2.2 Absorption.....	56
2.10.8.2.3 Band gap.....	57
2.11 Applications	58

Chapter 3

Experimental Methods and Techniques

3.1 Fabrication of porous silicon.....	60
3.2 Fabrication system.....	61
3.2.1 Lateral-wafer electrochemical cell.....	62
3.2.2 Bottom-wafer electrochemical cell.....	63
3.3 Porous silicon fabrication parameters (process).....	64
3.4 Silicon dioxide fabrication parameters (process)	64
3.5 Metallization.....	65
3.6 Measurements techniques.....	66
3.6.1 Morphological measurements.....	66
3.6.1.1 Scanning Electron Microscope (SEM).....	66
3.6.1.2 Gravimetric measurements (Porosity).....	68
3.6.2 Optical measurement.....	68
3.6.2.1 UV-Vis-NIR spectrophotometer	68

3.6.2.2 Photoluminescence measurements.....	69
3.6.3 Electrical Measurements.....	70
3.6.3.1 I-V measurement.....	71
3.4.3.2 Spectral Response and Quantum Efficiency measurement.....	71

Chapter 4:

Results and Discussion

4.1 Structural characterization.....	73
4.1.1 Scanning electron microscope (SEM)	73
4.1.2 Gravitational method.....	78
4.2 Optical properties.....	78
4.2.1 UV-Vis NIR Spectroscopy.....	78
4.2.1.1 Optical energy gap.....	80
4.2.2 Photoluminescence spectroscopy.....	82
4.2.3 Refractive index.....	84
4.3 Electrical properties.....	86
4.3.1 J-V characteristics under illumination	87
4.3.2 Quantum efficiency measurement:	89
4.3.2.1 Spectral response.....	89